

MAINTENANCE MANUAL  
FOR  
RF BOARD 800 MHz  
19D902123G16

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DESCRIPTION

RF Board 19D902123G16 is used in 800 MHz mobile combinations. The RF Board consists of the following circuits:

- A frequency synthesizer for generating the transmit carrier frequency and the receive circuit first mixer injection frequency.
- The transmit exciter, PA, and power control stages.
- The receive circuit front end, IF, and FM detector.
- Voltage regulators.

The RF Board is mounted in the bottom of the frame assembly. Refer to the appropriate Combination Manual for a mechanical layout of the radio.

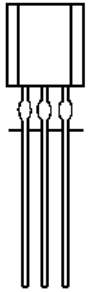
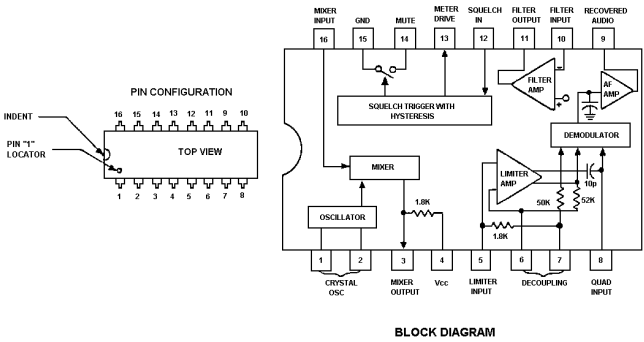
The transmitter and receiver adjustments are accessible from the top of the board. Chip components on the bottom of the board provide optimum RF performance, while being accessible for easy servicing by removing the friction fit bottom shields.

Selected use of sealed modules permits small board size as well as RF and mechanical protection for sensitive circuitry. Modules are not repairable and must be replaced if damaged.

IC DATA

IF AMPLIFIER/DETECTOR U501  
19A149980P3

VOLTAGE REGULATOR U502  
19A704073P2



BOTTOM VIEW  
PIN 1 - OUTPUT  
PIN 2 - GROUND  
PIN 3 - INPUT

# CIRCUIT ANALYSIS

## SYNTHESIZER CIRCUIT

The synthesizer generates all transmit and receive RF frequencies. A block diagram of the frequency synthesizer circuit is shown in Figure 1. The synthesizer uses a phase-locked VCO operating on the actual transmitter frequency of 806 to 825 MHz. In the direct (talk around) mode, the VCO is band shifted to operate at 851 to 870 MHz. The synthesizer's output signal is generated directly by VCO module U201 and buffered by transistors Q201 and Q205 to a level of +8 dBm (6 mW). This signal feeds the receiver mixer directly and is attenuated to +3 dBm by resistor R201 to feed the transmitter exciter module.

The synthesizer frequency is controlled by the microprocessor on the Logic Board. Frequency stability is maintained by temperature compensated crystal controlled oscillator (TCXO) module U204 operating at 12.8 MHz. The oscillator has a stability of 2.5 PPM (0.00025%) over the temperature range of -30° C to 75° C and determines the overall frequency stability of the radio.

The buffered VCO output from Q201 is further buffered by transistor Q204 to feed divide by 128/129 dual modulus prescaler U205. The prescaler feeds the F<sub>in</sub> input of the PLL U206. Within U206, the prescaler signal is further divided down to 12.5 kHz to be compared with a reference signal. This reference signal is derived from the 12.8 MHz TCXO module U204. U206 divides the 12.8 MHz signal down to the 12.5 kHz reference frequency.

Divider circuits in U206 are programmed by three inputs from the Logic Board, which are buffered and inverted by transistors Q208, Q209, and Q210. The **S ENABLE** pulse activates switch U202 to allow more rapid channel acquisition during channel changes.

A **LOCK DET** signal from the PLL goes to the microprocessor for processing to prevent transmission when the VCO is not on frequency and to provide an error message to the user.

When the radio is used in the direct (talk around) mode, the VCO is bandswitched to transmit in the 851 to 870 MHz range. The **BANDSWITCH** line from the microprocessor is normally at a logical high and switches low during transmit in direct mode. Transistor Q203 buffers and inverts this signal to feed the VCO and Q202. Transistor Q202 provides the 8 volt supply voltage to the receiver RF preamplifier which is switched off

when the **BANDSWITCH** line becomes active (logical low) during transmit in direct mode.

Audio modulation from the Audio Board is applied to the VCO module through **DEVIATION ADJUST** potentiometer R226 and buffer transistor Q211.

The synthesizer output drives the receiver mixer at +8 dBm, and is attenuated to +3 dBm for driving the exciter input.

## TRANSMITTER CIRCUIT

The transmitter consists of a fixed tuned, 200 milliwatt exciter module, a 10 watt PA module, a PIN diode switch, a low pass filter, a directional coupler, a power control circuit and a transmit voltage switch (see Figure 2).

### Exciter Module

Exciter Module A102 operates from a switched 8 volt supply. The exciter module bandwidth is sufficiently wide that both the 806 to 825 MHz and 851 to 870 MHz bands are allowed. No tuning is required. Both input and output ports operate at 50 ohms impedance. The exciter module provides typically 20 dB of gain and 200 milliwatts of output power to drive the power amplifier module.

### Power Amplifier Module

PA Module U101 requires a drive of 200 mW from the exciter module to deliver up to 10 watts output. The module is mounted to the rear heatsink. Input and output impedances are 50 ohms. The module output appears at J103 with a coax jumper either feeding J102 for a 10 watt radio or feeding a 25 watt PA Board.

The PA module output power is controlled by varying the DC voltage to the module's first stage. Refer to the power control circuit analysis below.

### Pin Diode Switch, Low Pass Filter And Directional Coupler

The transmitter output feeds J102 to feed PIN diode switch D104. In transmit, **SWITCHED 8V** is applied through resistors R123 and R124 and inductor L102, turning on PIN diodes D104 and D401. The DC path is completed through the coax jumper between J104 and J401 and through inductor L404. PIN diode D104 couples the transmitter power from J102 to the low pass filter. PIN diode D401 provides an RF path to ground to protect the receiver input.

The low pass filter reduces the harmonic output from the transmitter. The low pass filter feeds directional coupler

W101 and W102. The directional coupler provides a sample of transmitter power for the power control circuit. RF passes through the coupler to antenna jack J101.

### Power Control Circuit

The power control circuit samples the output power to maintain a constant power level across the band. Also, thermistors sense the heatsink temperature to throttle the power level down above +60° C. This circuit controls the supply voltage to the first amplifier stage in PA module U101.

The directional coupler (W101 and W102) provides a sample of transmitter power to diode D101. Diode D101, capacitors C102 and C103, resistors R125 and R106 and capacitor C104 produce a DC voltage proportional to the transmitter output power level. This DC voltage feeds U103 through the jumper on J105.

The DC level from the directional coupler feeds the (-) input of amplifier U103-B. Power set potentiometer R111 determines the DC level to the (+) input of U103-B. Amplifier U103-B amplifies the difference between the (-) and (+) inputs, forcing the output power level to equal the power set level by varying the drive to transistors Q101 and Q102. Transistor Q101 supplies the control voltage to PA module U101. For example, if the output power level begins to drop below the power set level, the output of U103-B increases positively, causing Q102 to conduct less. The base of Q101 rises, increasing the control voltage to the PA module, which increases the output power level back to the desired set level.

Thermistors R118 and R129, buffered by transistors Q106 and Q107, reduce the DC level to the (+) input of U103-B above 60° C. Transistor Q104, capacitor C123, and resistor R105 improve the transient stability of the power control loop when the transmitter is keyed.

### Transmit Switch

During transmit, the Logic Board microprocessor pulls the **DPTT** line low which is buffered by transistor Q105 before feeding U103-A. The output of U103-A goes low to turn on transistor Q103 which supplies **SWITCHED 8V** to the exciter module, the power control circuit, and the PIN diode switch. Use of jumper P106 installed on J106 allows EDAC's compatible Tx turn-on.

## RECEIVER CIRCUIT

The dual conversion receiver circuit consists of a front end section, a 45.0125 MHz first IF, and a 455 kHz second IF with a FM detector. All audio processing is accomplished on the Audio Board (see Figure 2.)

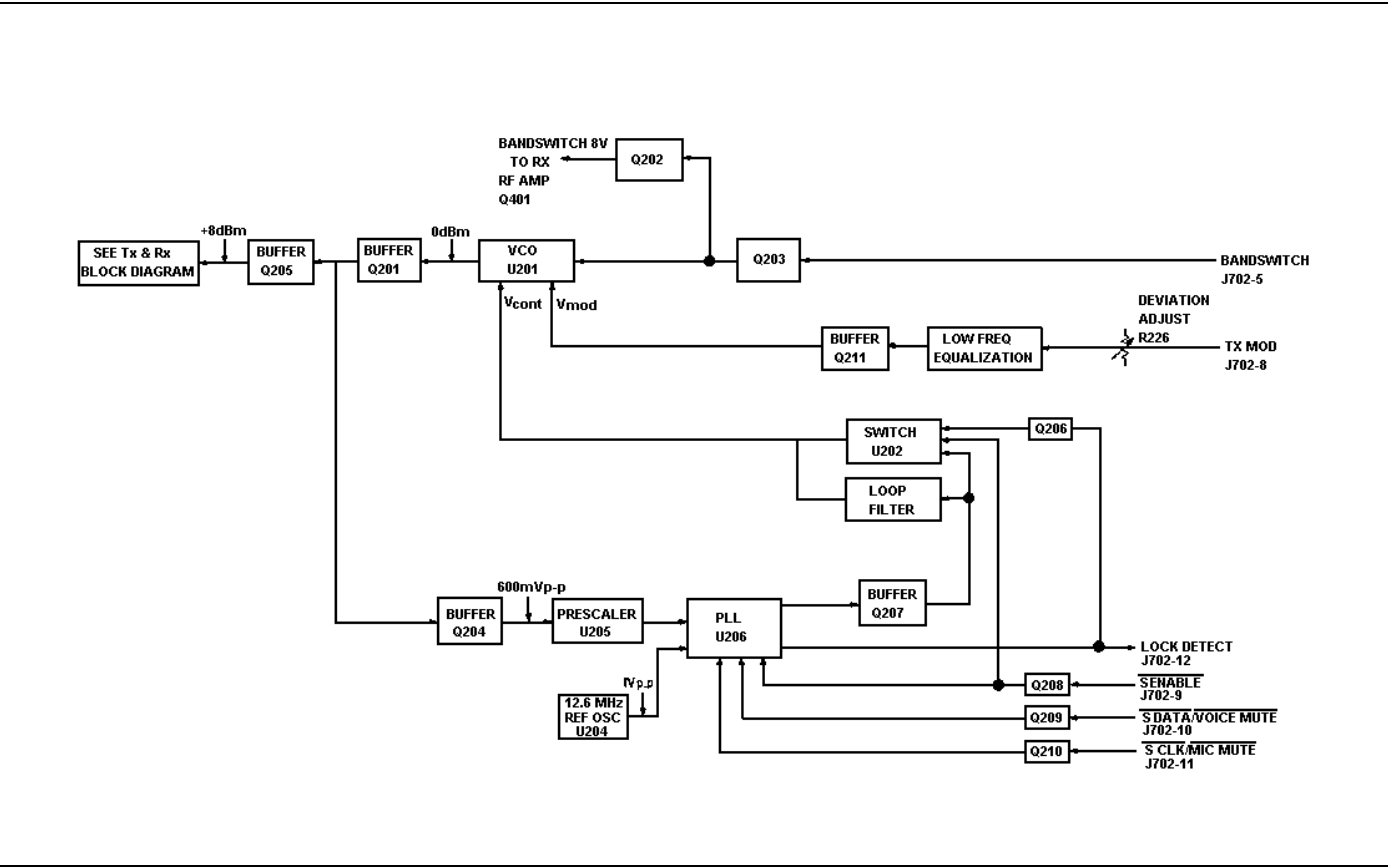


Figure 1- Synthesizer Block Diagram

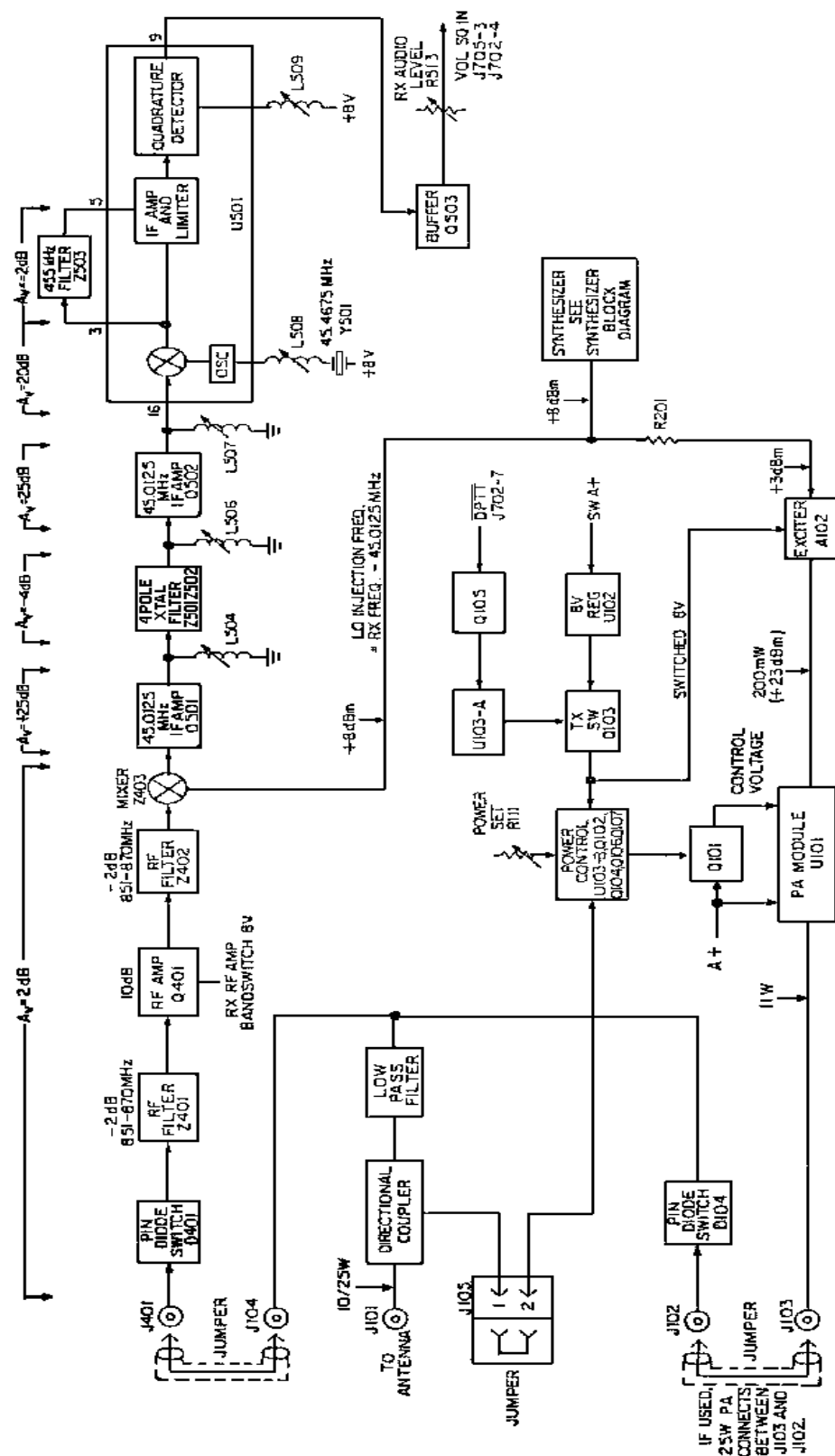


Figure 2 - Transmit And Receive Block Diagram

Front End Section

RF is coupled from antenna jack J101 through the directional coupler and the low pass filter to J104. J104 is jumpered to the receiver input at J401 feeding PIN diode D401. In transmit, SW 8V is applied through resistors R123 and R124 and through inductor L102, turning on PIN diodes D104 and D401. The DC path is completed through the coax jumper between J104 and J401 and through inductor L404. In transmit, PIN diode D401 provides a RF path to ground for the receiver input. In receive, D401 is off, allowing RF to pass by PIN diode D401 unattenuated.

RF selectivity is provided by two filters Z401 and Z402 on the input and output of RF amplifier transistor Q401. The filters are fixed tuned, 3 pole dielectric resonators with a bandwidth greater than 20 MHz to cover the 851 to 870 MHz band. About 2 dB of passband ripple is typical for this filter pair. Approximately 50 ohm impedance levels exist at the input and output ports of the filters.

RF Amplifier transistor Q401 is a low noise bipolar transistor biased with DC feedback. The feedback allows stable operating point of about 10 milliamperes, while allowing direct emitter grounding. Input matching is obtained with stripline L402. The amplifier load is primarily filter Z402. Capacitors C404, C405, and C410, and stripline L403 provide a low Q match to the filter. Transistor Q202 supplies 8 volts to the RF amplifier which is switched off when the BANDSWITCH line goes low while transmitting in direct mode.

Mixer Z403 is a doubly balanced diode mixer. This mixer is driven by a local oscillator signal from the synthesizer at +8 dBm to provide good intermodulation performance, spurious performance, and local oscillator isolation. The mixer conversion loss is typically 6 dB.

45.0125 MHz IF

The RF Board uses an IF which is offset by 1/2 channel at 45.0125 MHz. First IF amplifier transistor Q501 is a junction FET operated in the common gate mode. This configuration offers a typical input impedance of 75 ohms. The output circuitry is tuned by inductor L504 and loaded to provide the proper source termination for the four pole crystal filter which follows.

The output of the crystal filter is matched by second amplifier transistor Q502. This port is also tuned by inductor L506 and loaded to provide the proper source termination.

Transistor Q502 is a dual gate FET operating at a bias current of about 10 milliamperes. The output of Q502 is tuned by inductor L507 for maximum gain at 45.0125 MHz and is loaded by the second mixer in the U501 chip. This Q502 stage has a relatively high input and output impedance and has high isolation within the active device.

Converter/IF/Detector IC

IF Amplifier/Detector U501 is a MC3361 IC. Pins 1 and 2 connect to an internally biased oscillator transistor. Crystal Y501 and other external circuitry form a 45.4675 MHz third mode oscillator with the frequency adjusted by inductor L508. The oscillator drives the internal balanced mixer. The 45.0125 MHz IF signal is translated to 455 kHz and appears at Pin 3 of U501. This IF signal is filtered by 6 pole ceramic filter Z503 and drives the internal 455 kHz amplifier and limiter. The limited 455 kHz in turn drives an internal quadrature detector.

The phase shift network needed by the quadrature detector is provided by inductor L509. The audio output port is Pin 9 on U501. Inductor L509 is adjusted for maximum audio output level. The audio signal at Pin 9 is filtered by resistor R512 and capacitor C519 to reduce IF feedthrough. Buffer amplifier Q503 drives audio potentiometer R513 to set the amplitude of the VOL/SQ HI signal for proper system operation.

POWER DISTRIBUTION

The 13.8 Vdc source voltage is supplied to the RF Board through connectors J704 and feeds power control transistor Q101, PA module U101, and 20V transient suppressor D105. Diode D105 provides reverse polarity protection and protection from noise spikes and other overvoltage transients appearing on the input power cable.

Switched 13.6 volts (SW A+) is supplied to the RF Board through J704 and J705 and feeds regulators U102, U207, and U502. Regulator U102 supplies 8 volts to the transmitter switch, synthesizer 5 volt regulator U203 and to the Logic Board through J702. Regulator U207 supplies 8.3 volts to the synthesizer. Regulator U502 supplies 8 volts to the receiver.

SERVICE CHECKS

TRANSMITTER CIRCUIT

Most transmitter circuit problems can be isolated by checking the TX power gains shown in Figure 2 - RX and TX Block Diagram.

Transmitter Dc Measurements

1. First ensure that the DPTT is low when the microphone PTT is keyed low.
2. Check for approximately 8 Volts at L105 feeding the exciter module. If not present, troubleshoot the TX switch circuitry, Q103 and U103.
3. Check for approximately 7 volts across resistors R123 and R124. If not present, check pin diodes D104 and D401 and the conduction path from D401 to TX switch Q103.
4. Check for an adjustable voltage of 0 to 12 volts on Pin 2 of PA module U101. At maximum power, with Power Set adjustment R111 fully clockwise, Pin 2 should be at 12 volts. If not present, check the power control circuitry: U103, Q101, Q102, Q104, Q106 and Q107.
5. Check for 13.6 volts on Pins 3 and 4 of PA module U101 and ensure a good mechanical and electrical ground from the PA module to the bracket and casting.

RECEIVER CIRCUIT

To isolate a receiver circuit problem, refer to the Receiver Circuit Symptoms and check chart as follows:

RECEIVER CIRCUIT SYMPTOMS AND CHECKS

SYMPTOMS	CHECKS
No Audio	<div>1. U502 regulator</div> <div>2. The level and frequency of the first mixer injection frequency</div> <div>3. The level and frequency of the second mixer injection frequency</div> <div>4. Quadrature detector circuit</div> <div>5. Quadrature detector coil tuning</div>
Poor SINAD	<div>1. Consult Figure 2 - RX and TX Block Diagram for RX stage gains and troubleshoot</div> <div>2. Input cable</div> <div>3. Pin Diode switch shorted</div>
Distorted Audio	<div>1. Both mixer injection frequencies</div> <div>2. Quadrature detector coil tuning</div> <div>3. Crystal filter source and load tuning</div> <div>4. Z503: 455 kHz ceramic filter</div>

SYNTHESIZER CIRCUIT

Synthesizer troubleshooting consists of first, checking for the proper DC levels, then determining if the proper waveforms are present and checking individual modules.

DC Analysis

An 8.3 Vdc is supplied by regulator U207 and serves as the biasing voltage for transistor circuits Q201, Q204, Q205, Q206, Q207, Q208, Q209 and Q210. Resistor R211 decouples the 8.3 volts for use in VCO module U201. The 10 milliampere current drain of this module results in approximately 8.1 volts DC on Pin 4.

Regulator U203 uses the 8 volts from transmit regulator U102 to generate 5 volts for U204 and U205.

Waveforms

Synthesizer waveforms in Figures 3 through 8 were measured with a 10 megohm, 30 pf probe. Use DC coupling.

Module Isolation

Reference Oscillator U204:

Look for a waveform similar to the reference on Pin 2 (refer to Figure 3). If the waveform is not present, the oscillator module is probably defective.

VCO U201:

Connect a DC power supply to Pin 3. With 2.5 Vdc on Pin 3, the output of U201 (Pin 5) should be approximately 803 MHz. With 6.5 Vdc on Pin 3, the output should be approximately 828 MHz. Either transmit in direct mode or force the **BANDWIDTH** line to ground which will cause Pin 1 to go to 8 volts. The frequencies for 2.5 Vdc and 6.5 Vdc should be approximately 45 MHz higher.

Power output of the VCO can be measured by connecting a coax directly to the module, between Pin 5 and ground. The outputs should be approximately 0 dBm with C211 still connected in the circuit.

Prescaler U205:

Connect Pin 3 of the VCO to 4.5 Vdc. With the radio in receive, monitor the frequencies of the VCO at the connection of capacitor C201 and resistor R201. DC short Pin 7 of U205 to ground to cause divide by 129 to occur. The frequency output at Pin 5 should be the VCO frequency divided by 129. Tie Pin 7 to Pin 1(5 volts) to cause divide by 128 to occur. Check Pin 5 to verify that this occurs. Improper division may indicate a defective prescaler.

Bilateral Switch U202:

The bilateral switch is used to short around parts of the loop filter during channel scan. A shorted (to ground or adjacent gate) gate may be isolated by comparing voltages through the loop filter to those of a functioning radio. Defective gates might be suspected when the radio does not change frequency quickly enough.

Phase Lock-loop U206:

There are no other specific checks which aid in evaluation of U206. Usually, it is suspected only if all other checks are OK. Before changing, inspect chip components for mechanical damage and check resistances through the loop filter.

Transistor Q201 And Q205:

After checking for proper DC operation, measure the gain from VCO, Pin 5 to R201/C201. The gain should be approximately 8 dB.

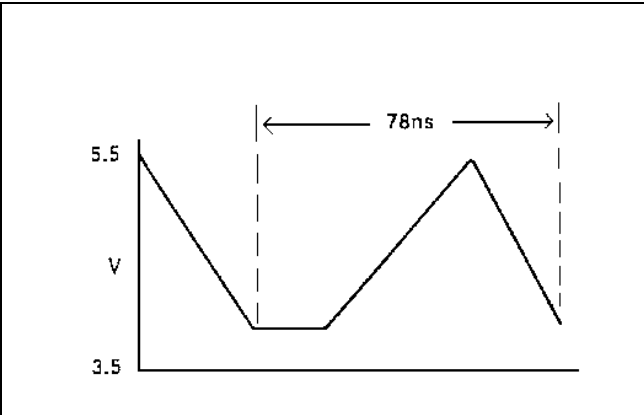


Figure 3 - Reference Oscillator (Input To U206, Pin 2)

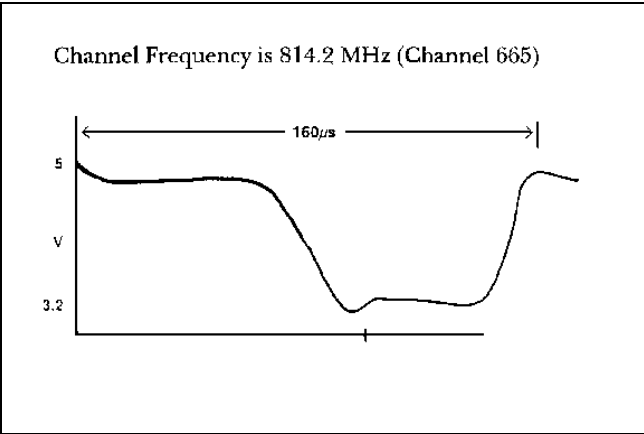


Figure 4 - Fin (input To U206, Pin 10)

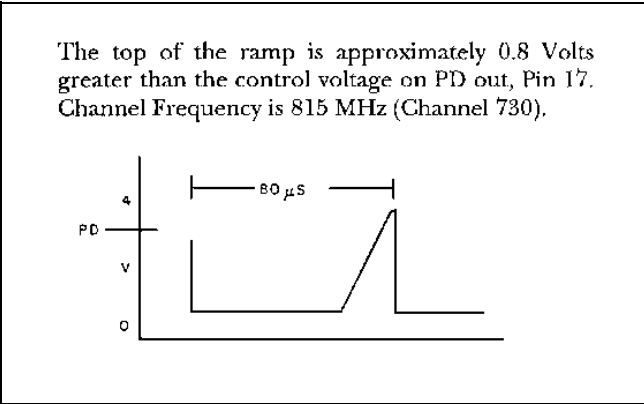


Figure 5 - **RAMP** (Generated in U206 and appears on Pin 15)

R  
F  
B  
O  
A  
R  
D

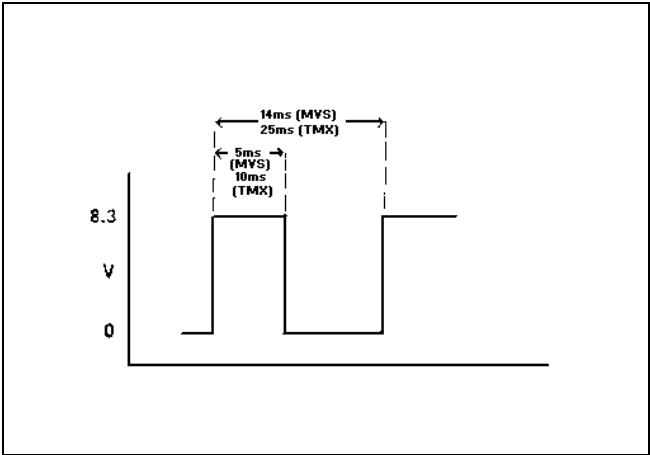


Figure 6 - **S ENABLE** (Input to U206, Pin 13) MVS Radio in SCAN on a single channel. TMX using Test Mode Function S 10.

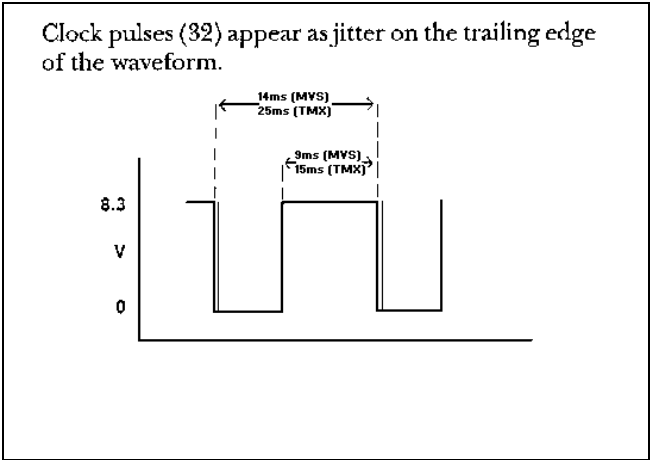


Figure 7 - **S CLOCK** (Input to U206, Pin 11) MVS radio in SCAN on a signal channel. TMX using Test Mode Function S 10.

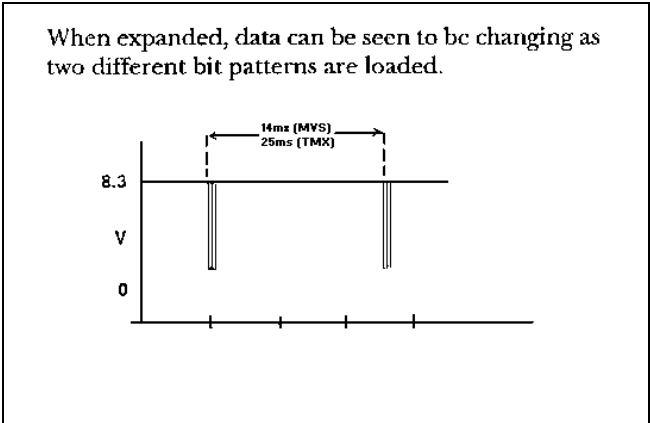


Figure 8 - **S DATA** (Input to U206, Pin 12) MVS Radio in SCAN on a Single Channel. TMX using Test Mode Function S 10.

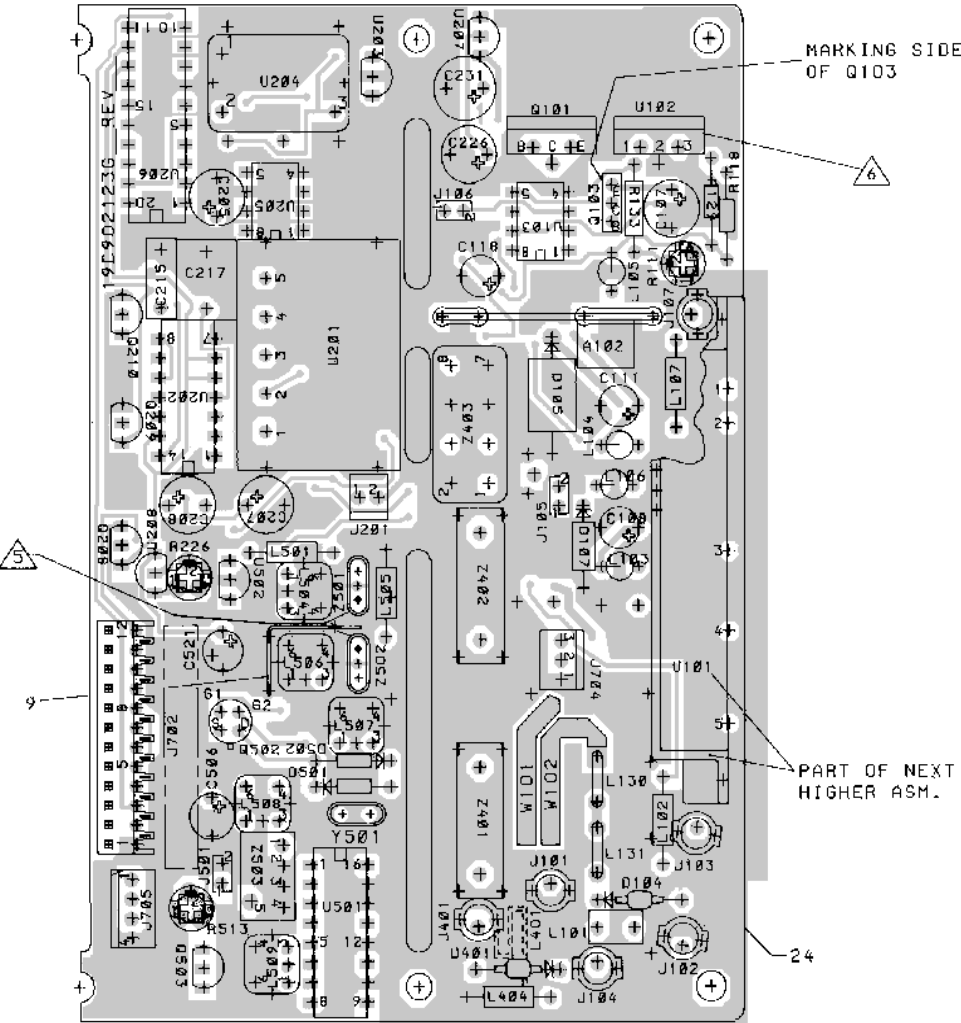
## PA MODULE REPLACEMENT

### To Remove PA Module U101

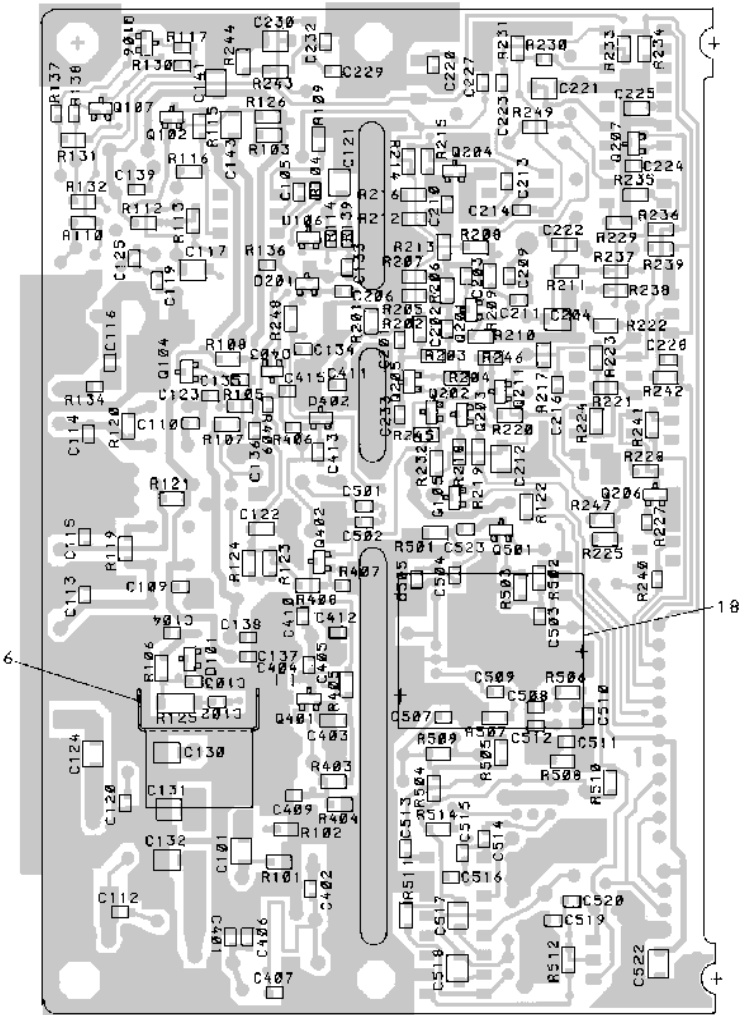
1. Unsolder the five leads from U101, using either solder removal braid, or a mechanical desoldering tool. These leads are fragile and can be bent very easily. **DO NOT** unsolder the shield that wraps around the module.
2. Remove the RF Board from the radio chassis assembly. Refer to the disassembly procedure provided in the Service Section. Carefully slide the module out of the shield and away from the board.

### To Install PA Module U101

1. Apply some silicone grease to the metal side of the replacement module.
2. Carefully insert the five leads from the module into the five corresponding printed wire board holes and slide the module into the shield. **DO NOT** solder the leads yet.
3. Slide the RF Board assembly back into the radio frame. Reinstall all hardware, harnesses, cables, etc. Replace all screws.
4. Install the two PA bracket screws before soldering.

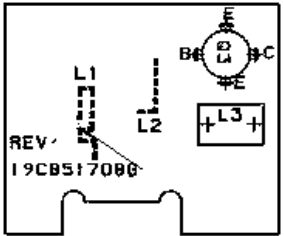


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(19D903566, COMP SIDE, Rev. 1A)

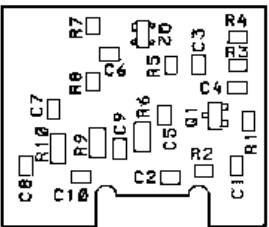


(19D902123, Sh. 5, Rev. 7)  
(19D903566, SOLDER SIDE, Rev. 1A)

EXCITER A102



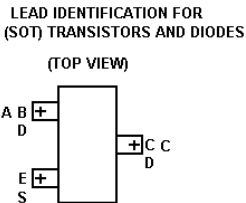
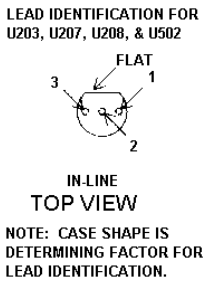
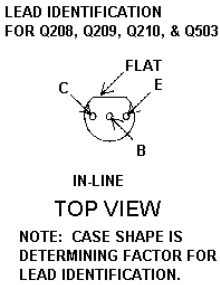
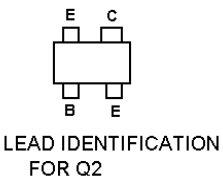
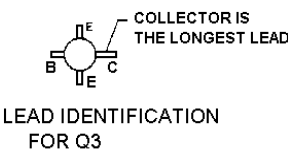
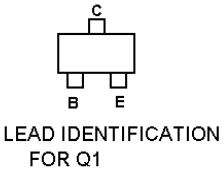
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VIEW OF BACKSIDE

(19C851708, Sh. 1, Rev. 0)

RF BOARD

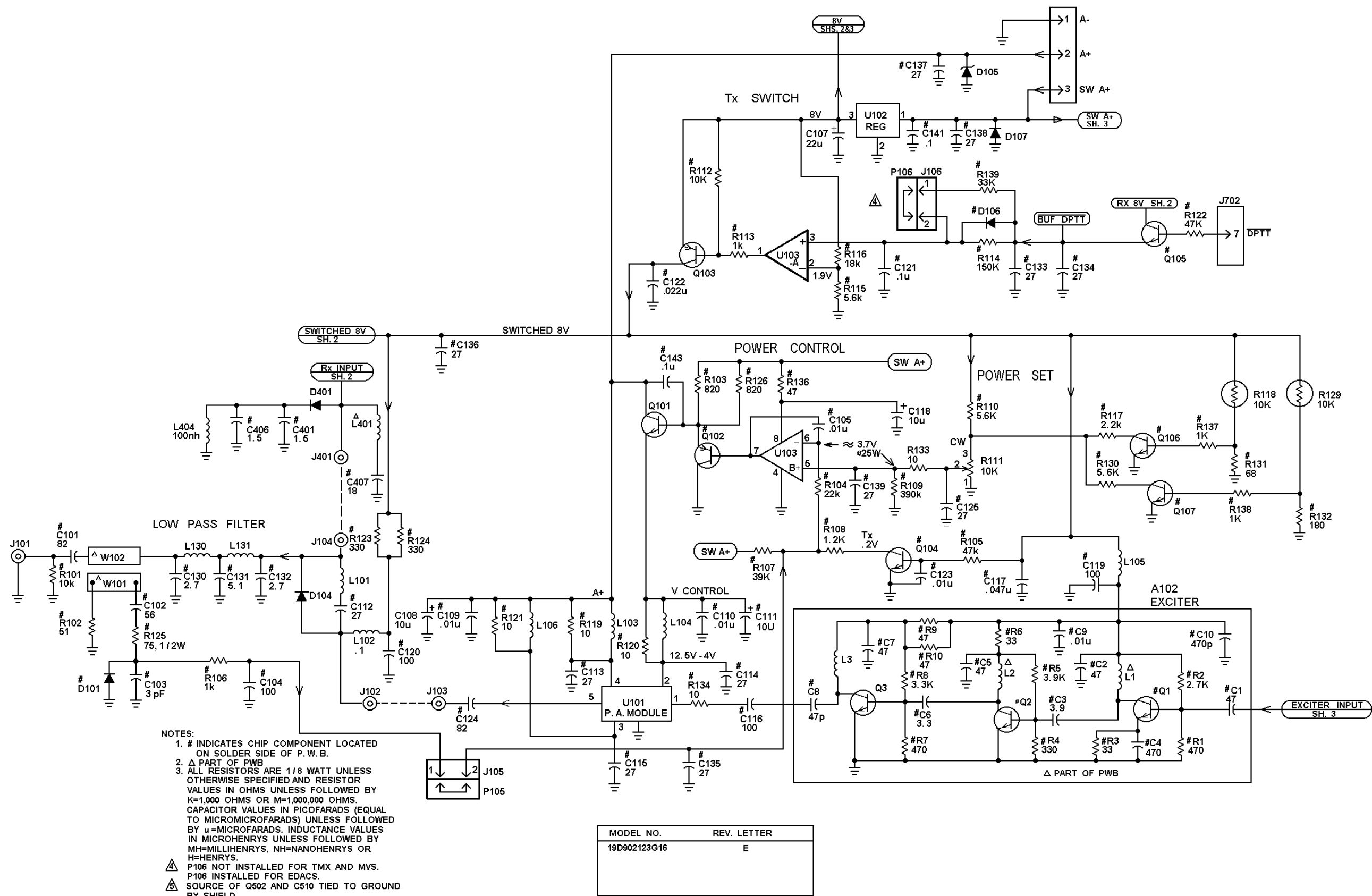


4. THE FOLLOWING ITEMS ARE MOS DEVICES REQUIRING SPECIAL CARE U202, U206.  
5. Z501 AND Z502 ARE A MATCHED PAIR OF CRYSTAL FILTERS WHICH MUST BE ORIENTED WITH "B" RESONATOR AS SHOWN. "B" RESONATOR IS IDENTIFIED BY DOT ON CAN.

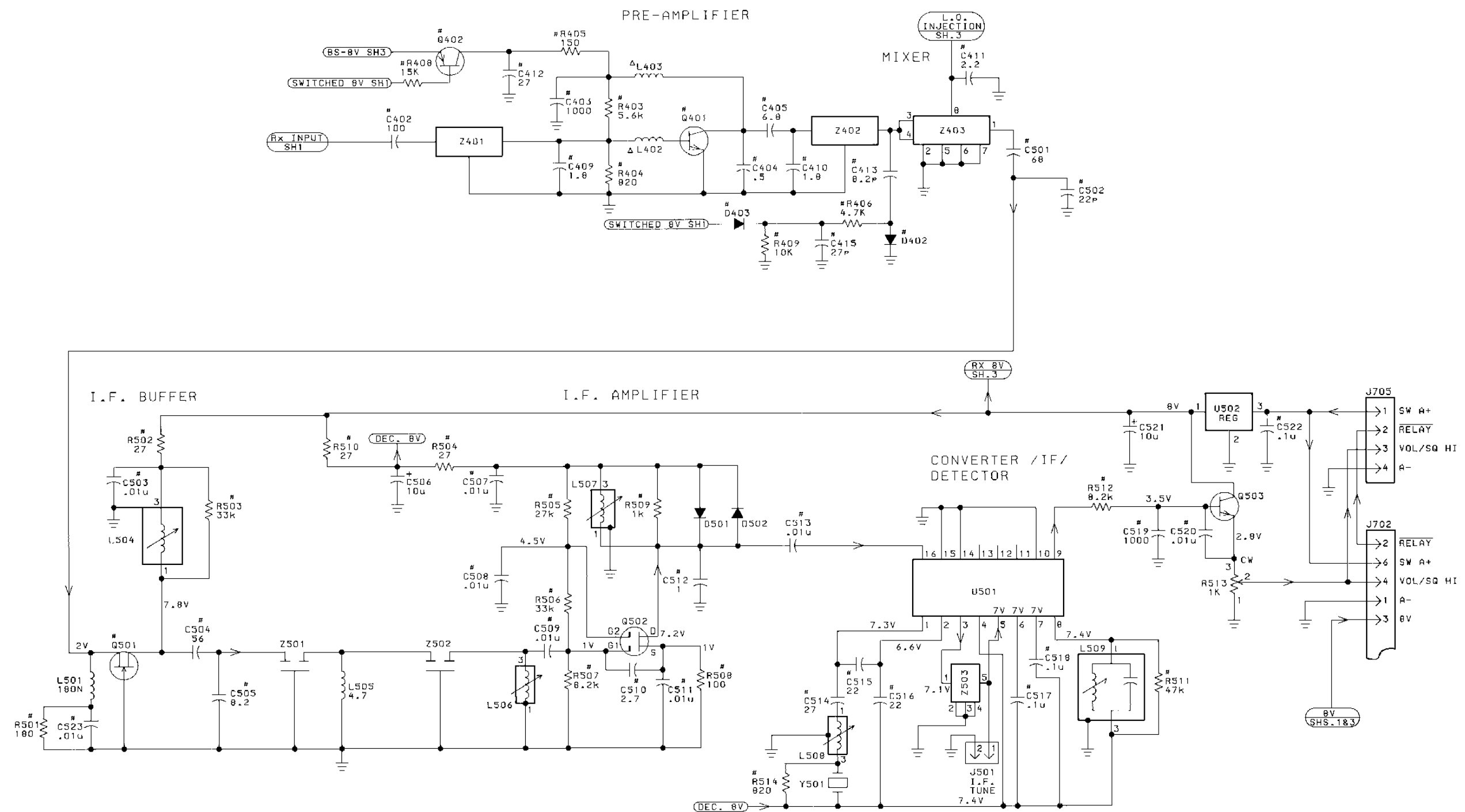


**CAUTION**  
OBSERVE PRECAUTIONS  
FOR HANDLING  
ELECTROSTATIC  
SENSITIVE  
DEVICES

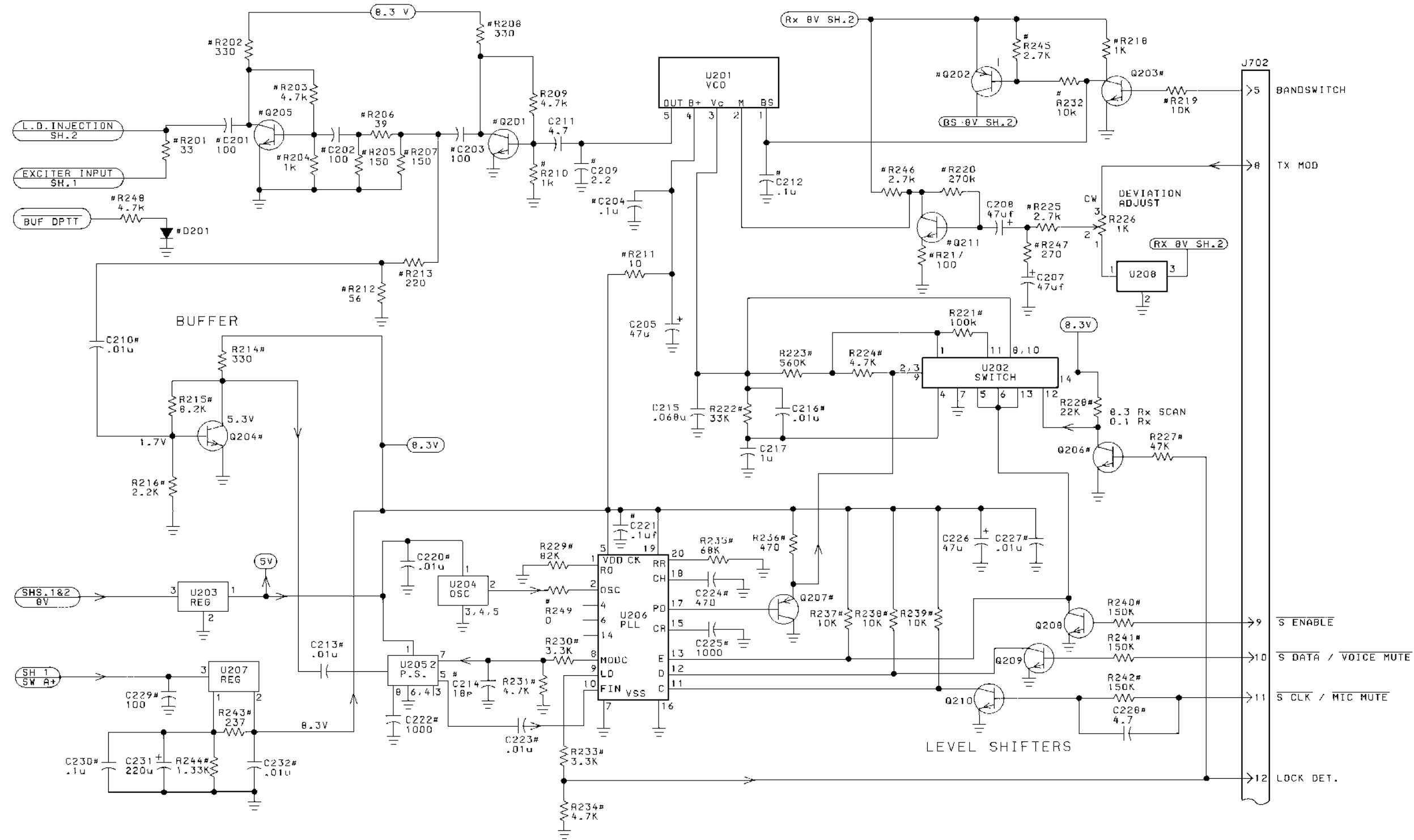
RF BOARD  
19D902123G16



RF BOARD  
19D902123G16







RF BOARD  
19D902123G16

(19D903565, Sh. 3, Rev. 7)

RF BOARD 19D902123G16 ISSUE 4		
SYMBOL	PART NO.	DESCRIPTION
A102		<b>EXCITER BOARD 19C851708G1</b>
----- CAPACITORS -----		
C1 and C2	19A702061P45	Ceramic: 47 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM.
C3	19A702061P8	Ceramic: 3.9 pF, ±5%, 50 VDCW, temp coef 0 ±120 PPM.
C4	19A702061P77	Ceramic: 470 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM.
C5	19A702061P45	Ceramic: 47 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM.
C6	19A702061P7	Ceramic: 3.3 pF, ±5%, 50 VDCW, temp coef 0 ±120 PPM.
C7 and C8	19A702061P45	Ceramic: 47 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM.
C9	19A702052P14	Ceramic: 0.01 μF ±10%, 50 VDCW.
C10	19A702061P45	Ceramic: 47 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM.
----- INDUCTORS -----		
L1 and L2		Part of Printed Wiring Board.
L3	19B800891P2	Coil, RF Choke: sim to Paul Smith SK-890-1.
----- TRANSISTORS -----		
Q1	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.
Q2	19A705436P1	Silicon, NPN: sim to Motorola MRF0211L.
Q3	19A701940P3	Silicon, NPN: sim to SRF-5116.
----- RESISTORS -----		
R1	19B801251P471	Metal film: 470 ohms, ±5%, 1/10w.
R2	19B801251P272	Metal film: 2.7K ohms, ±5%, 1/10w.
R3	19B801251P330	Metal film: 33 ohms, ±5%, 1/10w.
R4	19B801251P331	Metal film: 330 ohms, ±5%, 1/10w.
R5	19B801251P392	Metal film: 3.9K ohms, ±5%, 1/10w.
R6	19B800607P330	Metal film: 33 ohms, ±5%, 1/8w.
R7	19B801251P471	Metal film: 470 ohms, ±5%, 1/10w.
R8	19B801251P332	Metal film: 3.3K ohms, ±5%, 1/10w.
R9 and R10	19B800607P470	Metal film: 47 ohms, ±5%, 1/8w.
----- CAPACITORS -----		
C101	19A705108P35	Mica: 82 pF, ±5%, 500 VDCW, temp coef 0 ±50 PPM/°C.
C102	19A702061P49	Ceramic: 56 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
*C103	19A702236P12	Ceramic: 3.0 pF, ±0.25pF, 50 VDCW, temp coef 0 ±30 PPM/°C.
C104	19A702061P61	Ceramic: 100 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C105	19A702052P14	Ceramic: 0.01 μF, ±10%, ±50 VDCW.
C107	19A701534P8	Tantalum: 22 μF, ±20%, 10 VDCW.

SYMBOL	PART NO.	DESCRIPTION
C109 and C110	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C111	19A703314P10	Electrolytic: 10 μF, -10, +50%, 50 VDCW; sim to Panasonic LS Series.
C112 thru C115	19A702061P33	Ceramic: 27 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C116	19A702061P61	Ceramic: 100 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C117	19A702052P22	Ceramic: 0.047 μF, ±10%, 50 VDCW.
C118	19A703314P10	Electrolytic: 10 μF, -10, +50%, 50 VDCW; sim to Panasonic LS Series.
C119 and C120	19A702061P61	Ceramic: 100 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C121	19A702052P26	Ceramic: 0.1 μF, ±10%, 50 VDCW.
C122	19A702052P28	Ceramic: 0.022 μF, ±10%, 50 VDCW.
C123	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C124	19A705108P35	Mica: 82 pF, ±5%, 500 VDCW, temp coef 0 +50 PPM/°C.
C125	19A702061P33	Ceramic: 27 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C130	19A705108P201	Mica: 1 pF, ±.25 pF, 500 VDCW, temp coef 0 +200 PPM/°C.
C131	19A705108P3	Mica: 3.9 pF, ±.25 pF, 500 VDCW, temp coef 0 +200 PPM/°C.
C132	19A705108P201	Mica: 1 pF, ±.25 pF, 500 VDCW, temp coef 0 +200 PPM/°C.
C133 thru C139	19A702061P33	Ceramic: 27 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C141	19A702052P26	Ceramic: 0.1 F, ±10%, 50 VDCW.
C143	19A702052P26	Ceramic: 0.1 F, ±10%, 50 VDCW.
C201 thru C203	19A702061P61	Ceramic: 100 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C205	19A701534P17	Tantalum: 47 μF, ±20%, 10 VDCW.
C207 and C208	19A701534P17	Tantalum: 47 μF, ±20%, 10 VDCW.
C209	19A70061P5	Ceramic: 2.2 pF, ±5%, 50 VDCW, temp coef 0 ±120 PPM/°C.
C210	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C211	19A702061P9	Ceramic: 4.7 pF, ±5%, 50 VDCW, temp coef 0 ±60 PPM/°C.
C212	19A702052P26	Ceramic: 0.1 μF, ±10%, 50 VDCW.
C213	19A702052P14	Ceramic: 0.01μ F, ±10%, 50 VDCW.
C214	19A702061P25	Ceramic: 18 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C215	19A700004P1	Metalized polyester: 0.068 μF, ±10%, 63 VDCW.
C216	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C217	19A700004P11	Metalized polyester: 1.0 μF, ±10%, 63 VDCW.
C220	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C221	19A702052P26	Ceramic: 0.1 μF, ±10%, 50 VDCW.
C222	19A702061P99	Ceramic: 1000 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C223	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C224	19A702061P77	Ceramic: 470pF, ±5%, 50 VDCW temp coef 0 ±30 PPM/°C.
C225	19A702061P99	Ceramic: 1000 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C226	19A701534P17	Tantalum: 47 μF, ±20%, 10 VDCW.
C227	19A702052P14	Ceramic: 0.01μ F, ±10%, 50 VDCW.

SYMBOL	PART NO.	DESCRIPTION
C228	19A702061P9	Ceramic: 4.7 pF, ±5%, 50 VDCW, temp coef 0 ±60 PPM/°C.
C229	19A702061P61	Ceramic: 100 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C230	19A702052P26	Ceramic: 0.1 μF, ±10%, 50 VDCW.
C231	19A703314P2	Tantalum: 220 μF, -10 +50%, 10 VDCW.
C232	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C401	19A702236P8	Ceramic: 1.5 pF, ±0.25 pF, 50 VDCW.
C402	19A702061P61	Ceramic: 100 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C403	19A702061P99	Ceramic: 1000 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C404	19A702236P1	Ceramic: 0.5 pF, ±0.1 pF, 50 VDCW, temp coef 0 ±30 PPM/°C.
C405	19A702236P21	Ceramic: 6.8 pF, ±0.5 pF, 50 VDCW, temp coef 0 ±60 PPM/°C.
C406	19A702236P8	Ceramic: 1.5 pF, ±.25 pF, 50 VDCW.
C407	19A702061P25	Ceramic: 18 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C409 and C410	19A702236P9	Ceramic: 1.8 pF, ±0.25 pF, 50 VDCW, temp coef 0 ±30 PPM/°C.
C411	19A702236P10	Ceramic: 2.2 pF, ±2.5 pF, 50 VDCW, temp coef 0 ±30 PPM/°C.
C412	19A702061P33	Ceramic: 27 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C413	19A702061P12	Ceramic: 8.2 pF, ±0.5 pF, 50 VDCW, temp coef 0 ±60 PPM/°C.
C415	19A702061P33	Ceramic: 27 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C501	19A702061P53	Ceramic: 68 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C502	19A702061P29	Ceramic: 22 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C503	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C504	19A702061P49	Ceramic: 56 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C505	19A702061P12	Ceramic: 8.2 pF, ±0.5 pF, 50 VDCW, temp coef 0 ±60 PPM/°C.
C506	19A701534P7	Tantalum: 10 μF, ±20%, 16 VDCW.
C507 thru C509	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C510	19A702061P6	Ceramic: 2.7 pF, ±0.5 pF, 50 VDCW, temp coef 0 ±120 PPM/°C.
C511	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C512	19A702061P1	Ceramic: 1 pF, ±0.5 pF, 50 VDCW.
C513	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C514	19A702061P33	Ceramic: 1000 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C515 and C516	19A702061P29	Ceramic: 22 pF, ±5%, 50 VDCW, temp coef 0 ±30 PPM/°C.
C517 and C518	19A702052P26	Ceramic: 0.1 μF, ±10%, 50 VDCW.
C519	19A702052P5	Ceramic: 1000 pF, ±10%, 50 VDCW.
C520	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.
C521	19A703314P10	Electrolytic: 10 μF, -10, +50%, 50 VDCW; sim to Panasonic LS Series.
C522	19A702052P26	Ceramic: 0.1 μF, ±10%, 50 VDCW.
C523	19A702052P14	Ceramic: 0.01 μF, ±10%, 50 VDCW.

SYMBOL	PART NO.	DESCRIPTION
----- DIODES -----		
D101	19A705377P1	Silicon, Hot Carrier: sim to MMB0201.
D104	19J706892P2	Silicon, PIN: sim to UM9401.
D105	19A703588P3	Zener, transient suppressor: sim to 1N6278A.
D106	19A134587P2	Silicon: 2 diodes, common cathode; sim to BAV 70.
D107	T324ADP1041	Silicon: rectifier; sim to 1N4004.
D201	19A702525P2	Silicon, PIN: sim to MMBV3401.
D401	19J706892P2	Silicon, PIN: sim to UM9401.
D402	19A702525P2	Silicon, PIN: sim to MMBV3401.
D403	19A134587P2	Silicon: 2 diodes, common cathode; sim to BAV 70.
D501 and D502	19A700028P1	Silicon: 75 mA, 75 PIV; sim to 1N4148.
----- JACKS -----		
J101 thru J104	19B801341P1	RF Jack.
J105 and J106	19A700072P1	Printed wire: 2 contacts rated @ 2.5 amps; sim to Molex 22-03-2021.
J401	19B801341P1	RF Jack.
J501	19A700072P1	Printed wire: 2 contacts rated @ 2.5 amps; sim to Molex 22-03-2021.
J702	19A704779P11	Connector: sim to Molex 22-17-2122.
J704	19A700072P29	Printed wire: 3 contacts rated at 2.5 amps; sim to Molex 22-27-2031.
J705	19A700072P30	Printed wire: 4 contacts rated at 2.5 amps; sim to Molex 22-27-2041.
----- INDUCTORS -----		
L101	19B800891P2	Coil, RF Choke: sim to Paul Smith SK-890-1.
L102	19A700024P1	Coil, RF: 100 nH, ±10%, 0.08 ohms DC res max., 100v.
L103 thru L106	19A704921P1	Coil.
L130 and L131	19A703775P6	Coil.
L401 thru L403		Part of Printed Wiring Board.
L404	19A700024P1	Coil, RF: 100 nH, ±10%, 0.08 ohms DC res max., 100v.
L501	19A700024P4	Coil, RF: 180nH, ±10%.
L504	19B801413P4	Coil: 39 MHz.
L505	19B209420P21	Coil, RF: 4.7 H, ±5%, 1.20 ohms DC res max; sim to Jeffers 4436-8J.
L506 thru L508	19B801413P4	Coil: 39 MHz.
L509	19B801415P2	Transformer, 455 kHz: sim to AEPD 162B3277P17.

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\*COMPONENTS, ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

SYMBOL	PART NO.	DESCRIPTION
----- TRANSISTORS -----		
Q101	344A3225P1	Silicon, NPN: sim to Motorola MJF3055.
Q102	19A703197P2	Silicon, PNP: sim to MMBT4403 Low Profile Pkg.
Q103	19A704972P1	Silicon, PNP: sim to Motorola 2N4918.
Q104 thru Q107	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.
Q201	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.
Q202	19A700059P2	Silicon, PNP: sim to MMBT3906.
Q203	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.
Q204 and Q205	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.
Q206	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.
Q207	19A700059P2	Silicon, PNP: sim to MMBT3906.
Q208	19A700023P2	Silicon, NPN: sim to 2N3904.
Q209 and Q210	19A702084P2	Silicon, NPN: sim to MPS 2369.
Q211	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.
Q401	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.
Q402	19A700059P2	Silicon, PNP: sim to MMBT3906.
Q501	19A702524P2	N-Type, field effect: sim to MMBFU310.
Q502	19A116818P3	N Channel, field effect: sim to Type 3N1877.
Q503	19A700023P2	Silicon, NPN: sim to 2N3904.
----- RESISTORS -----		
R101	19B800607P103	Metal film: 10K ohms, ±5%, 1/8w.
R102	19B800607P510	Metal film: 51 ohms, ±5%, 1/8w.
R103	19B800607P821	Metal film: 820 ohms, ±5%, 1/8w.
R104	19B801251P223	Metal film: 22K ohms, ±5%, .1w.
R105	19B800607P473	Metal film: 47K ohms, ±5%, 1/8w.
R106	19B800607P102	Metal film: 1K ohms, ±5%, 1/8w.
R107	19B800607P393	Metal film: 39K ohms, ±5%, 1/8w.
R108	19B800607P122	Metal film: 1.2K ohms, ±5%, 1/8w.
R109	19B800607P394	Metal film: 390K ohms, ±5%, 1/8w.
R110	19B800607P562	Metal film: 5.6K ohms, ±5%, 1/8w.
R111	19B800779P10	Variable: 10K ohms, ±25%, 100 VDCW, .3w.
R112	19B800607P103	Metal film: 10K ohms, ±5%, 1/8w.
R113	19B800607P102	Metal film: 1K ohms, ±5%, 1/8w.
R114	19B801251P154	Metal film: 150K ohms, ±5%, .1w.
R115	19B800607P562	Metal film: 5.6K ohms, ±5%, 1/8w.
R116	19B800607P183	Metal film: 18K ohms, ±5%, 1/8w.
R117	19B801251P222	Metal film: 2.2K ohms, ±5%, .1w.
R118	19A701864P4	Thermal 10K ohms ±10%;sim to Midwest Components 2H-103.
R119 thru R121	19B800607P100	Metal film: 10 ohms, ±5%, 1/8w.
R122	19B800607P473	Metal film: 47K ohms, ±5%, 1/8w.
R123 and R124	19B800607P331	Metal film: 330 ohms, ±5%, 1/8w.
R125	19B801486P750	Metal film: 75 ohms, ±5%, 1/2w.
R126	19B801607P821	Metal film: 820 ohms, ±5%, 1/8w.
R129	19A701864P4	Thermal 10K ohms ±10%;sim to Midwest Components 2H-103.
R130	19B801251P562	Metal film: 5.6K ohms, ±5%, .1w.
R132	19B800607P181	Metal film: 180 ohms, ±5%, 1/8w.

SYMBOL	PART NO.	DESCRIPTION
R133	19A700106P15	Composition: 10 ohms, ±5%, 1/4w.
R134	19B801251P100	Metal film: 10 ohms, ±5%, .1w.
R136	19B801251P470	Metal film: 47 ohms, ±5%, .1w.
R137 and R138	19B801251P102	Metal film: 1K ohms, ±5%, 1/10w.
R139	19B801251P333	Metal film: 33K ohms, ±5%, 1/10w.
R201	19B800607P330	Metal film: 33 ohms, ±5%, 1/8w.
R202	19B800607P331	Metal film: 330 ohms, ±5%, 1/8w.
R203	19B800607P472	Metal film: 4.7K ohms, ±5%, 1/8w.
R204	19B800607P102	Metal film; 1K ohms, ±5%, 1/8w.
R205	19B800607P151	Metal film: 150 ohms, ±5%, 1/8w.
R206	19B800607P390	Metal film: 39 ohms, ±5%, 1/8w.
R207	19B800607P151	Metal film: 150 ohms, ±5%, 1/8w.
R208	19B800607P331	Metal film: 330 ohms, ±5%, 1/8w.
R209	19B800607P472	Metal film: 4.7K ohms, ±5%, 1/8w.
R210	19B800607P102	Metal film: 1K ohms, ±5%, 1/8w.
R211	19B800607P100	Metal film: 10 ohms, ±5%, 1/8w.
R212	19B800607P560	Metal film: 56 ohms, ±5%, 1/8w.
R213	19B800607P221	Metal film: 220 ohms, ±5%, 1/8w.
R214	19B800607P331	Metal film: 330 ohms, ±5%, 1/8w.
R215	19B800607P822	Metal film: 8.2K ohms, ±5%, 1/8w.
R216	19B800607P222	Metal film: 2.2K ohms, ±5%, 1/8w.
R217	19B800607P101	Metal film: 100 ohms, ±5%, 1/8w.
R218	19B800607P102	Metal film: 1K ohms, ±5%, 1/8w.
R219	19B800607P103	Metal film: 10K ohms, ±5%, 1/8w.
R220	19B800607P274	Metal film: 270K ohms, ±5%, 1/8w.
R221	19B800607P104	Metal film: 100K ohms, ±5%, 1/8w.
R222	19B800607P333	Metal film: 33k ohms, ±5%, 1/8w.
R223	19B800607P564	Metal film: 560K ohms, ±5%, 1/8w.
R224	19B800607P472	Metal film: 4.7K ohms, ±5%, 1/8w.
R225	19B800607P272	Metal film: 2.7K ohms, ±5%, 1/8w.
R226	19B800779P4	Variable: 1K ohms ±25%, 100 VDCW, 0.3w.
R227	19B801251P473	Metal film: 47K ohms, ±5%, 1/10w.
R228	19B800607P223	Metal film: 22K ohms, ±5%, 1/8w.
R229	19B800607P823	Metal film: 82K ohms, ±5%, 1/8w.
R230	19B801251P332	Metal film: 3.3K ohms, ±5%, 1/10w.
R231	19B800607P472	Metal film: 4.7K ohms, ±5%, 1/8w.
R232	19B800607P103	Metal film: 10K ohms, ±5%, 1/8w.
R233	19B800607P332	Metal film: 3.3K ohms, ±5%, 1/8w.
R234	19B800607P472	Metal film: 4.7K ohms, ±5%, 1/8w.
R235	19B800607P683	Metal film: 68K ohms, ±5%, 1/8w.
R236	19B800607P471	Metal film: 470 ohms, ±5%, 1/8w.
R237 thru R239	19B800607P103	Metal film: 10K ohms, ±5%, 1/8w.
R240	19B801251P154	Metal film: 150K ohms, ±5%, 1/10w.
R241 and R242	19B800607P154	Metal film: 150K ohms, ±5%, 1/8w.
R243	19A702931P137	Metal film: 237 ohms, ±1%, 200 VDCW, 1/8w.
R244	19A702931P213	Metal film: 1330 ohms, ±1%, 200 VDCW, 1/8w.
R245 and R246	19B800607P272	Metal film: 2.7K ohms, ±5%, 1/8w.
R247	19B800607P271	Metal film: 270 ohms, ±5%, 1/8w.
R248	19B800607P472	Metal film: 4.7K ohms, ±5%, 1/8w.
R249	19B800607P1	Metal film: jumper.

SYMBOL	PART NO.	DESCRIPTION
R403	19B800607P562	Metal film: 5.6K ohms, ±5%, 1/8w.
R404	19B800607P821	Metal film: 820 ohms, ±5%, 1/8w.
R405	19B800607P151	Metal film: 150 ohms, ±5%, 1/8w.
R406	19B801251P472	Metal film: 4.7k ohms, ±5%, 1/10w.
R408	19B800607P153	Metal film: 15K ohms, ±5%, 1/8w.
R409	19B801251P103	Metal film: 10K ohms, ±5%, 1/10w.
R501	19B800607P181	Metal film: 180 ohms, ±5%, 1/8w.
R502	19B800607P270	Metal film: 27 ohms, ±5%, 1/8w.
R503	19B800607P333	Metal film: 33K ohms, ±5%, 1/8w.
R504	19B800607P270	Metal film: 27 ohms, ±5%, 1/8w.
R505	19B800607P273	Metal film: 27K ohms, ±5%, 1/8w.
R506	19B800607P333	Metal film: 33K ohms, ±5%, 1/8w.
R507	19B800607P822	Metal film: 8.2K ohms, ±5%, 1/8w.
R508	19B800607P101	Metal film: 100 ohms, ±5%, 1/8w.
R509	19B800607P102	Metal film: 1K ohms, ±5%, 1/8w.
R510	19B800607P270	Metal film: 27 ohms, ±5%, 1/8w.
R511	19B800607P473	Metal film: 47K ohms, ±5%, 1/8w.
R512	19B800607P822	Metal film: 8.2K ohms, ±5%, 1/8w.
R513	19B800779P4	Variable: 1K ohms, ±25%, 100 VDCW, .3w.
R514	19B800607P821	Metal film: 820 ohms, ±5%, 1/8w.
----- INTEGRATED CIRCUITS -----		
U101	19A705645P1	Power Amplifier Module.
U102	19A134717P3	Linear: 8V regulator; sim to MC7808CT.
U103	19A701789P2	Linear: Dual Op Amp; sim to LM358.
U202	19A700029P44	Digital: Bilateral Switch.
U203	19A704971P1	Linear: +5V Regulator; sim to MC78L05ACP.
U204	19B801351P7	Temperature Compensated Crystal Oscillator, 12.80 MHz ±1 PPM/Yr.
U205	19A704740P1	Digital: Divider; sim to Mitsubishi M54475P.
U206	19B800902P4	Digital: Synthesizer, CMOS Serial Input.
U207	19A701999P4	Linear, (Positive Voltage Regulator): sim to LM317LZ.
U208	19A704971P1	Linear: +5V Regulator; sim to MC78L05ACP.
U501	19A149980P3	Linear: Osc/Mixer/IF/Det/Amp.
U502	19A704073P2	Linear: 8V Regulator; sim to MC78L08CP.

SYMBOL	PART NO.	DESCRIPTION
----- CABLES -----		
W101 and W102		Part of Printed Wiring Board.
----- CRYSTALS -----		
Y501	19A705376P7	Crystal, Fixed Frequency: 45.4675 MHz, ±10 PPM.
----- FILTERS -----		
Z401 and Z402	19A704888P1	Bandpass Filter, 851-871 MHz: sim to Murata DFC3R861P020BTD.
Z403	19B801025P2	Balanced Mixer: sim to Mini-Circuits SBL-1X.
Z501	19A705328P2	Monolithic Crystal: 45.0125 MHz; sim to Toyocom 45EZ2B2.
Z502		Part of Z501.
Z503	19B801021P2	Bandpass Filter: 455 kHz ±1.5; sim to Murata CFW-455E.
----- MISCELLANEOUS -----		
6	19B801490P1	Ground Strap.
9	19B801566P1	Shield.
18	19B801566P2	Shield.

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter" which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for the descriptions of parts affected by these revisions.

**REV. A - RF BOARD 19D902123G16**  
To insure output power flatness across entire transmit frequency band, capacitor C103 was changed.  
C103 was 4.7 pF (19A702061P9)

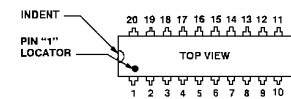
**REV. B - RF BOARD 19D902123G16**  
To improve RF flatness across talkaround band.  
C103 changed from 3.9 pF (19A702061P8) to 3 pF (19A702236P12).

**REV. C - RF BOARD 19D902123G16**  
To increase power adjust range. R111 was 2.2K ohms (19B800779P6).

**REV. D - RF BOARD 19D902123G16**  
U501 was replaced. Was 19A704619P1. Replaced with 19A704619P3.

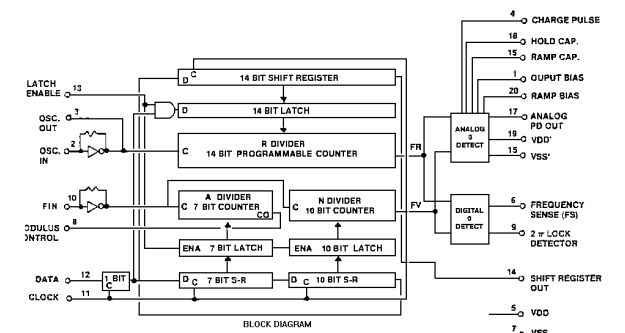
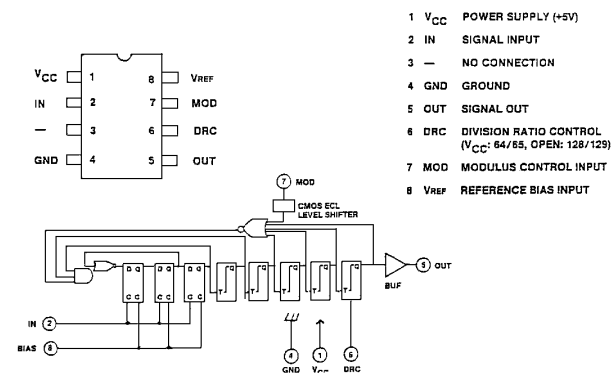
**REV. E - RF BOARD 19D902123G16**  
Working parameters of old part changed. U501 was 19A704619P3.  
Changed to 19A149980P3.

**SYNTHESIZER U206**  
**19B800902P4**



- | PIN DESCRIPTION                    |    |    |                       |
|------------------------------------|----|----|-----------------------|
| OUTPUT BIAS                        | 1  | 20 | RAMP BIAS             |
| OSC. IN                            | 2  | 19 | VDD <sup>1</sup>      |
| OSC. OUT                           | 3  | 18 | VOLD <sup>1</sup>     |
| CHARGE PWLSE                       | 4  | 17 | ANALOG PD OUT         |
| VDD                                | 5  | 16 | VSS <sup>1</sup>      |
| (FS) FREQ. SENSE                   | 6  | 15 | RAMP CAP.             |
| VSS                                | 7  | 14 | SHIFT REGISTER OUTPUT |
| MODULUS CONTROL                    | 8  | 13 | LATCH ENABLE          |
| 2 <sup>2</sup> $\pi$ LOCK DETECTOR | 9  | 12 | DATA IN               |
| FIN                                | 10 | 11 | CLOCK                 |

**DIGITAL DIVIDER U205**  
19A704740P1



**VOLTAGE REGULATOR U208**  
**19A704971P1**



- PIN IDENTIFICATION**  
**PIN 1. OUTPUT**  
**PIN 2. GROUND**  
**PIN 3. INPUT**